Substitute for Form 1449A/PTO (Modified)

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Sheet

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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of

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	Com	plete if Known	100
	Application Number	09/831,539	<u> </u>
	Filing Date	04/15/2002	C confid
	First Named Inventor:	Anand S. Murthy	DEC 1 7 2002
	Group Art Unit	2823	E &
	Examiner Name	Kebede, Brook	& TRADENIARIE
	Attorney Docket Number	42390P6624US	

				U.S. PATENT DOCUMENTS		
Exam. Initial*	Cite No.1	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant
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-							<u> </u>

Examiner		Date Considered
Signature	Brook Kepede	3/8/2007

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Sneet		Attorney Docket Number 42390P6624US	
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Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
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BL		Written Opinion for PCT/US99/26224, mailed October 30, 2000, 4 pages.	

Examiner			Date	1 - 1 -
Signature	Brook	Kekedl	Considered	3/8/2002

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